

## AMENDMENT

### Amendments to the Specification:

Please replace existing paragraph [0079] with the following amended paragraph:

[0079]        Embodiment 2

By oxidizing the silicon layer 25 using the surface wave plasma in which Kr/O<sub>2</sub> is 97%/3% using the plasma processing unit 10 shown in Fig. 1, a silicon oxide film 41 of 4 nm thickness was formed on the surface of the silicon layer 25. Then, a silicon oxide film (SiO<sub>2</sub>) 42 of 50 nm was deposited on the silicon oxide film 41 by a plasma enhanced chemical vapor growth method (PECVD). A chemical vapor deposition apparatus with an electro magnetic wave generator of a VHF band and a gaseous mixture with of tetraethylorthosilicate (hereinafter to be called "TEOS") and O<sub>2</sub> was used for the deposition. An aluminum electrode was formed on the silicon oxide film 42 to produce a capacitor, and an interface state density was measured from the capacitance-voltage (C-V) characteristics.